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High Output Power Si MOS FET (Discrete)

■30MHz Band

Type Number	Structure	Max.ratings		Vdd (V)	f (MHz)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		VDSS (V)	Pch (W)						
RD00HHS1*	Si,MOS	30	3.1	12.5	30	0.004	0.3	55	SOT-89
RD06HHF1*	Si,MOS	50	34.7	12.5	30	0.15	6	55	TO-220
RD16HHF1*	Si,MOS	50	62.5	12.5	30	0.4	16	55	TO-220
RD70HHF1*	Si,MOS	50	150	12.5	30	3.5	70	55	Ceramic(Large)
RD100HHF1*	Si,MOS	50	176.5	12.5	30	7	100	55	Ceramic(Large)

Tc=25°C

*:New product

■175/520MHz Band

Type Number	Structure	Max.ratings		Vdd (V)	f (MHz)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		VDSS (V)	Pch (W)						
RD00HVS1 *	Si,MOS	30	3.1	12.5	175	0.005	0.5	50	SOT-89
RD01MUS1*	Si,MOS	30	3.6	7.2	520	0.03	0.8	50	SOT-89
RD02MUS1*	Si,MOS	30	21.9	7.2	175/520	0.05/0.05	2/2	55/50	SLP
RD07MVS1 *	Si,MOS	30	50	7.2	175/520	0.3/0.7	7/7	55/50	SLP
RD15HVF1 *	Si,MOS	30	59.5	12.5	175/520	0.6/3	15/15	55/50	TO-220
RD30HVF1 *	Si,MOS	30	75	12.5	175	1	30	55	Ceramic(Small)
RD30HUF1 *	Si,MOS	30	75	12.5	520	3	30	50	Ceramic(Small)
RD70HVF1 *	Si,MOS	30	150	12.5	175/520	6/10	70/50	55/50	Ceramic(Large)
RD60HUF1 *	Si,MOS	30	150	12.5	520	10	60	50	Ceramic(Large)

Tc=25°C

*:New product

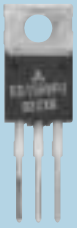
■900MHz Band

Type Number	Structure	Max.ratings		Vdd (V)	f (MHz)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		VDSS (V)	Pch (W)						
RD45HMF1*	Si,MOS	30	125	12.5	900	15	45	45	Ceramic(Large)

Tc=25°C

*:New product

SOT-89



TO-220

SLP

Ceramic (Small)

Ceramic (Large)

Type Number

■High Output Power Si MOS FET (Discrete)

RD 07 M V S 1

- 1: ●Si MOS FET (Discrete)
- 07: ●Output Power (W)
- M: ●Operation Voltage (V)

Symbol	Voltage
M	7.2V
N	9.6V
H	12.5V

- V: ●Frequency Range (MHz)

Symbol	Frequency Range
H	30MHz
V	175MHz
U	520MHz
M	800MHz

- S: ●Outline

Symbol	Segment
S	Mold
F	Flange

- RD: ●Suffix

Note:Type number show the outline of products. For detail specification, Please confirm a formal specification.

High Output Power Si MOS FET Module

■66-88MHz Band

Type Number	Max.ratings Vdd(V)	f (MHz)		Vdd (V)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		min	max					
RA07H0608M *	13.2	68	88	12.5	0.03	7	38	H46S
RA30H0608M *	17	68	88	12.5	0.05	30	40	H2S

Tc=25°C

*:New product

■135-175MHz Band

Type Number	Max.ratings Vdd(V)	f (MHz)		Vdd (V)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		min	max					
RA07M1317M *	9.2	135	175	7.2	0.02	6.5	45	H46S
RA08N1317M *	12.5	135	175	9.6	0.02	8	50	H46S
RA08H1317M *	13.2	135	175	12.5	0.02	8	40	H46S
RA13H1317M *	17	135	175	12.5	0.05	13	40	H2S
RA30H1317M *	17	135	175	12.5	0.05	30	40	H2S
RA60H1317M *	17	135	175	12.5	0.05	60	40	H2S
RA35H1516M *	17	154	162	12.5	0.05	40	50	H2S

Tc=25°C

*:New product

■215-270MHz Band

Type Number	Max.ratings Vdd(V)	f (MHz)		Vdd (V)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		min	max					
RA07M2127M *	9.2	215	270	7.2	0.02	7	45	H46S
RA30H2127M *	17	210	270	12.5	0.05	30	40	H2S

Tc=25°C

*:New product

■330-520MHz Band

Type Number	Max.ratings Vdd(V)	f (MHz)		Vdd (V)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		min	max					
RA07M3340M *	9.2	330	400	7.2	0.05	7	40	H46S
RA07M4047M *	9.2	400	470	7.2	0.05	7	40	H46S
RA07M4452M *	9.2	440	520	7.2	0.05	7	40	H46S
RA07N3340M *	12.5	330	400	9.6	0.02	7.5	43	H46S
RA07N4047M *	12.5	400	470	9.6	0.02	7.5	43	H46S
RA07N4452M *	12.5	440	520	9.6	0.02	7.5	43	H46S
RA07H3340M *	13.2	330	400	12.5	0.02	7	40	H46S
RA07H4047M *	13.2	400	470	12.5	0.02	7	40	H46S
RA07H4452M *	13.2	440	520	12.5	0.02	7	40	H46S
RA13H3340M *	17	330	400	12.5	0.05	13	40	H2S
RA13H4047M *	17	400	470	12.5	0.05	13	40	H2S
RA13H4452M *	17	440	520	12.5	0.05	13	40	H2S
RA30H3340M *	17	330	400	12.5	0.05	30	40	H2S
RA30H4045MR *	17	400	450	12.5	0.05	30	40	H2RS
RA30H4047M *	17	400	470	12.5	0.05	30	40	H2S
RA30H4452M *	17	440	520	12.5	0.05	30	40	H2S
RA45H4047M *	17	400	470	12.5	0.05	45	35	H2S
RA45H4045MR *	17	400	450	12.5	0.05	45	35	H2RS
RA45H4452M *	17	440	520	12.5	0.05	45	35	H2S

Tc=25°C

*:New product

■900MHz Band

Type Number	Max.ratings Vdd(V)	f (MHz)		Vdd (V)	Pin (W)	Po(min) (W)	nd(min) (%)	Package outline
		min	max					
RA03M8087M *	9.2	806	870	7.2	0.05	3.6	32	H46S
RA03M8894M *	9.2	889	941	7.2	0.05	3.6	32	H46S
RA06H8285M *	17	820	851	12.5	0.001	6	35	H11S
RA13H8891MA *	17	889	915	12.5	0.2	13	30	H2S
RA13H8891MB *	17	880	915	12.5	0.001	13	35	H11S
RA20H8087M *	17	806	870	12.5	0.05	20	25	H2S
RA20H8994M *	17	896	941	12.5	0.05	20	25	H2S

Tc=25°C

*:New product

H46S

H2S

H11S

Type Number

■High Output Power Si MOS FET Module

RA 07 M 4452 M

- ●Module
- ●Output Power (W)
- ●Operation Voltage (V)

Symbol	Voltage
M	7.2V
N	9.6V
H	12.5V

- ●Frequency Range (MHz)

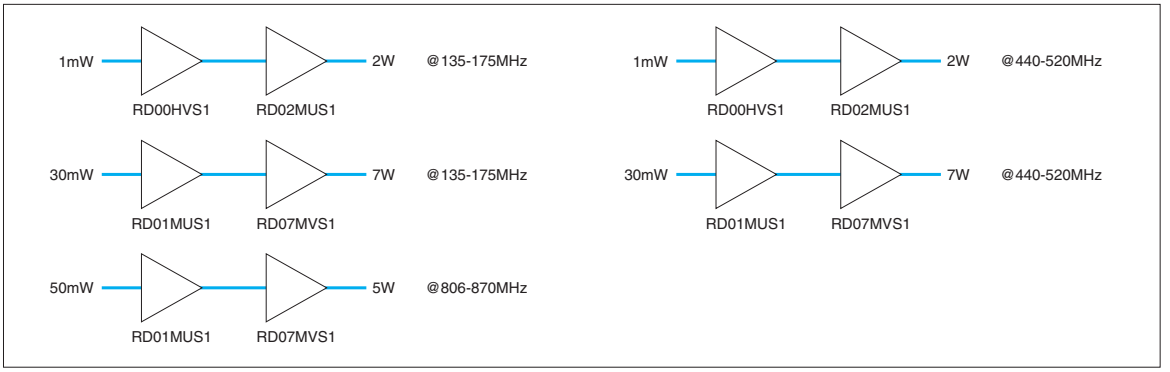
Symbol (Example)	Frequency Range (Example)
4452	440~520MHz
1317	135~175MHz

- ●Frequency Unit

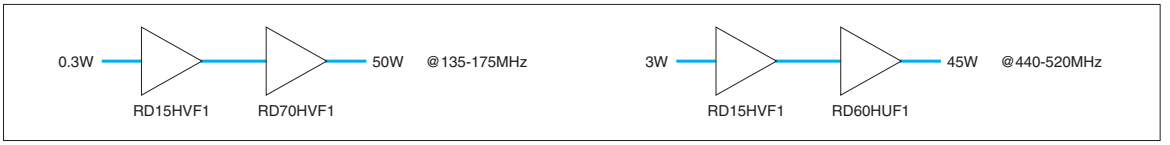
Symbol	Unit
M	MHz
G	GHz

Note:Type number show the outline of products. For detail specification, Please confirm a formal specification.

VHF~800MHz Band 7.2V operation Recommended Line up



VHF~UHF Band 12.5V operation Recommended Line up



Application Note

AN-GEN-001	Characteristics for silicon Compound
AN-GEN-006	Precautions and Recommendations for MITSUBISHI RF POWER MODULES
AN-GEN-026	Electro Static Sensitivity for Mitsubishi RF Module RA**** series
AN-GEN-034	Recommended mounted & precaution for RD07MVS1 & RD02MUS1
AN-GEN-038	Test Result of surge tolerance of RD-series
AN-GEN-039	Thermal resistance of RD02MUS1
AN-UHF-017	RD02MUS1 RF characteristic data
AN-UHF-018	RD07MVS1 RF characteristic data
AN-UHF-019	RD01MUS1 RF characteristic data
AN-UHF-023	RD07MVS1 Thermal Resistance

Precautions

MITSUBISHI ELECTRIC's Si RF Power Products are designed for consumer Mobile Communication terminals.
Please contact Mitsubishi Electronic Corporation or an authorized MITSUBISHI semiconductor product distributor when considering the use without above application.